

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-250	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	-0.21	--	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -250\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	$\mu\text{A}$
		$V_{DS} = -200\text{ V}, T_C = 125^\circ\text{C}$	--	--	-10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-3.0	--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -1.55\text{ A}$	--	1.63	2.1	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -40\text{ V}, I_D = -1.55\text{ A}$ (Note 4)	--	2.0	--	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	325	420	pF
$C_{oss}$	Output Capacitance		--	65	85	pF
$C_{rss}$	Reverse Transfer Capacitance		--	10	13	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -125\text{ V}, I_D = -4.0\text{ A},$ $R_G = 25\text{ }\Omega$  (Note 4, 5)	--	9.5	30	ns
$t_r$	Turn-On Rise Time		--	60	130	ns
$t_{d(off)}$	Turn-Off Delay Time		--	14	40	ns
$t_f$	Turn-Off Fall Time		--	27	65	ns
$Q_g$	Total Gate Charge	$V_{DS} = -200\text{ V}, I_D = -4.0\text{ A},$ $V_{GS} = -10\text{ V}$  (Note 4, 5)	--	10.3	14	nC
$Q_{gs}$	Gate-Source Charge		--	2.7	--	nC
$Q_{gd}$	Gate-Drain Charge		--	5.2	--	nC

**Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current	--	--	-3.1	A		
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-12.4	A		
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -3.1 A	--	--	-5.0	V	
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -4.0 A,	(Note 4)	--	140	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		--	0.64	--	μC

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 46.6\text{ mH}$ ,  $I_{AS} = -3.1\text{ A}$ ,  $V_{DD} = -50\text{ V}$ ,  $R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -4.0\text{ A}$ ,  $dI/dt \leq 300\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\text{ }\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

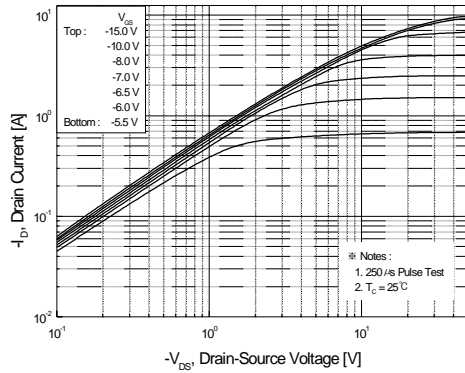


Figure 1. On-Region Characteristics

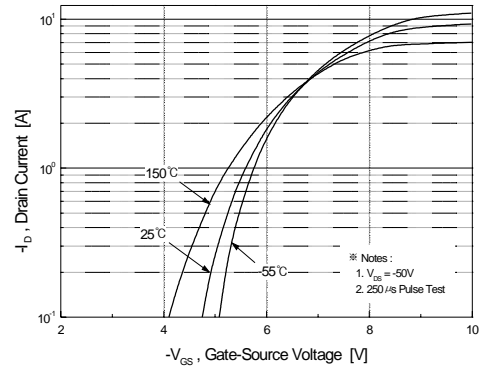


Figure 2. Transfer Characteristics

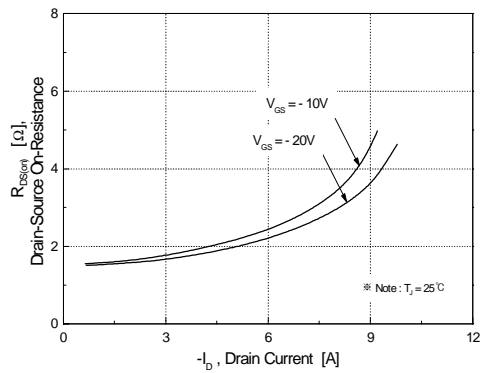


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

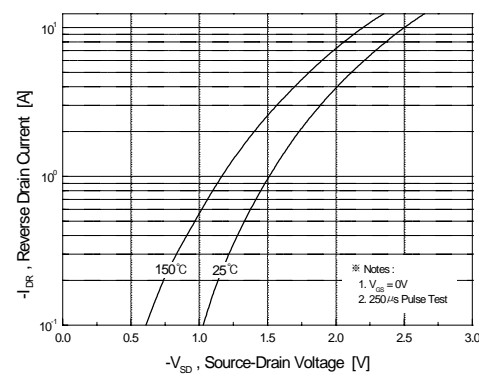


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

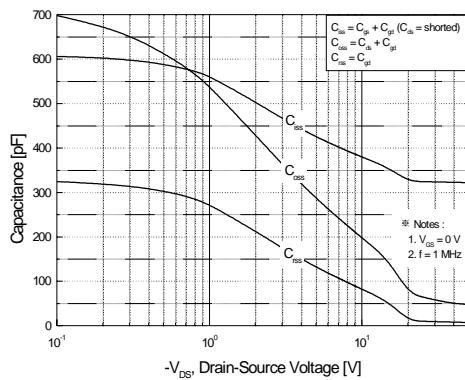


Figure 5. Capacitance Characteristics

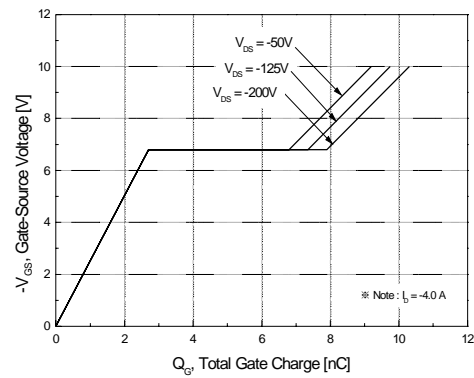
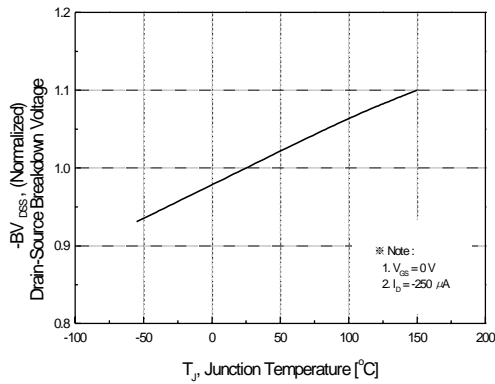
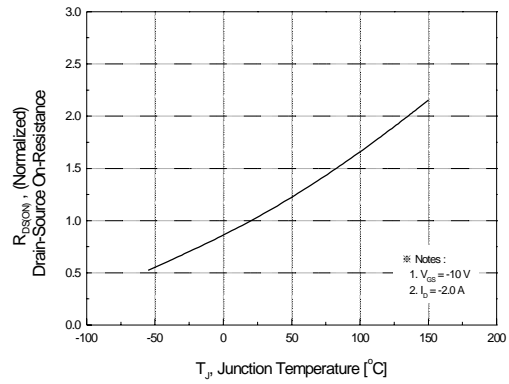


Figure 6. Gate Charge Characteristics

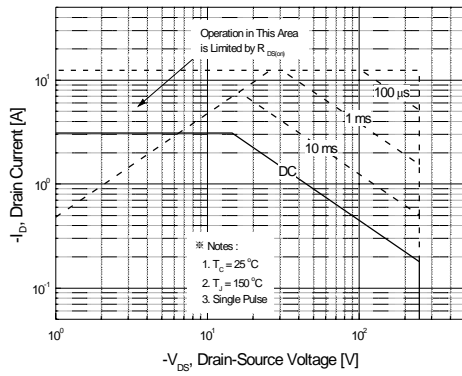
## Typical Characteristics (Continued)



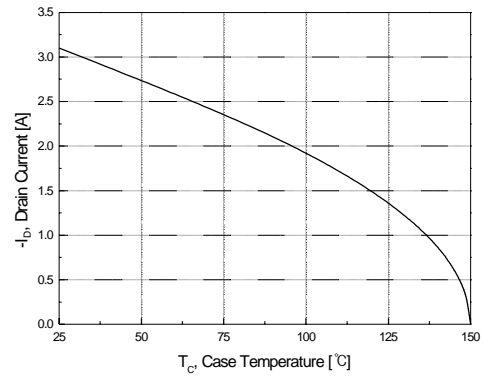
**Figure 7. Breakdown Voltage Variation vs. Temperature**



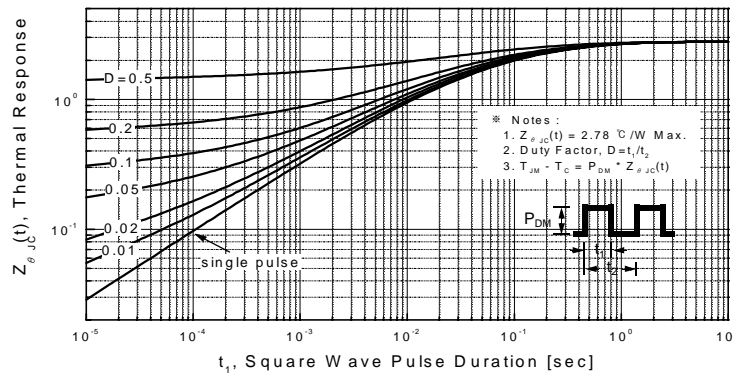
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**

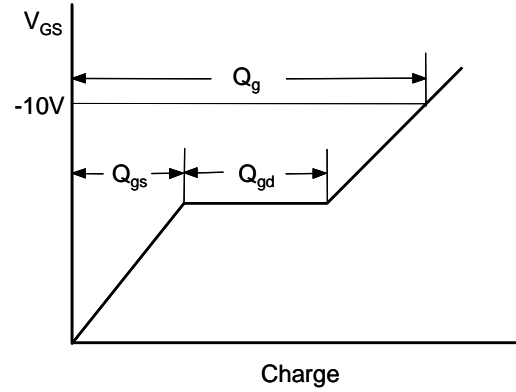
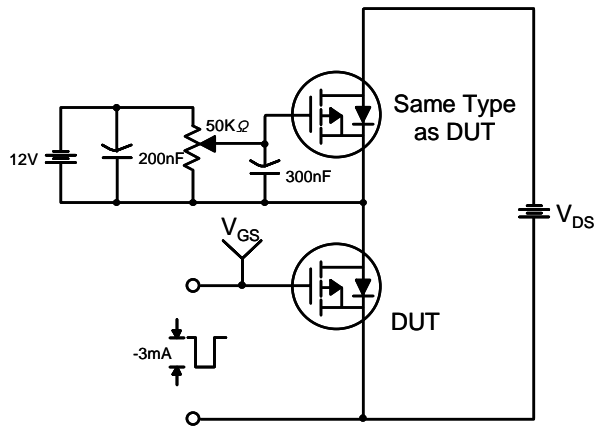


**Figure 10. Maximum Drain Current vs. Case Temperature**

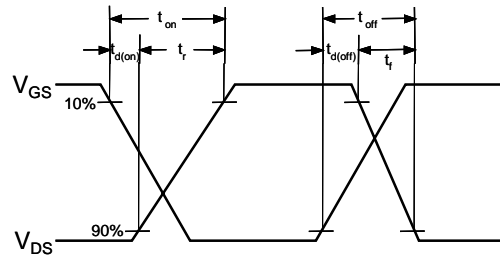
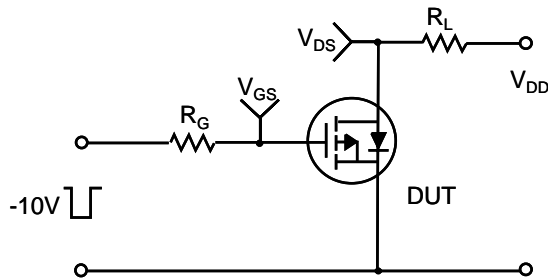


**Figure 11. Transient Thermal Response Curve**

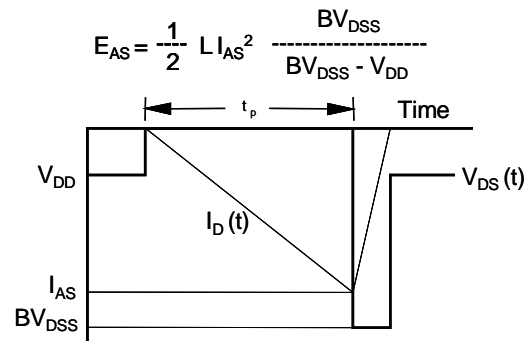
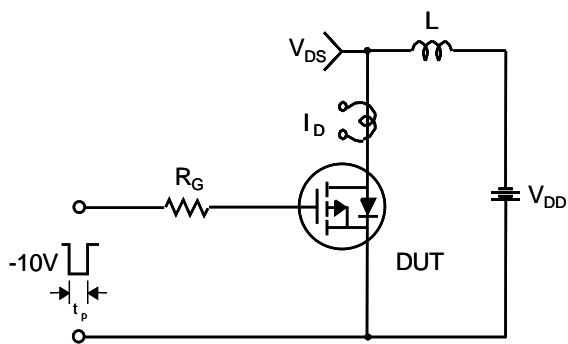
### Gate Charge Test Circuit & Waveform



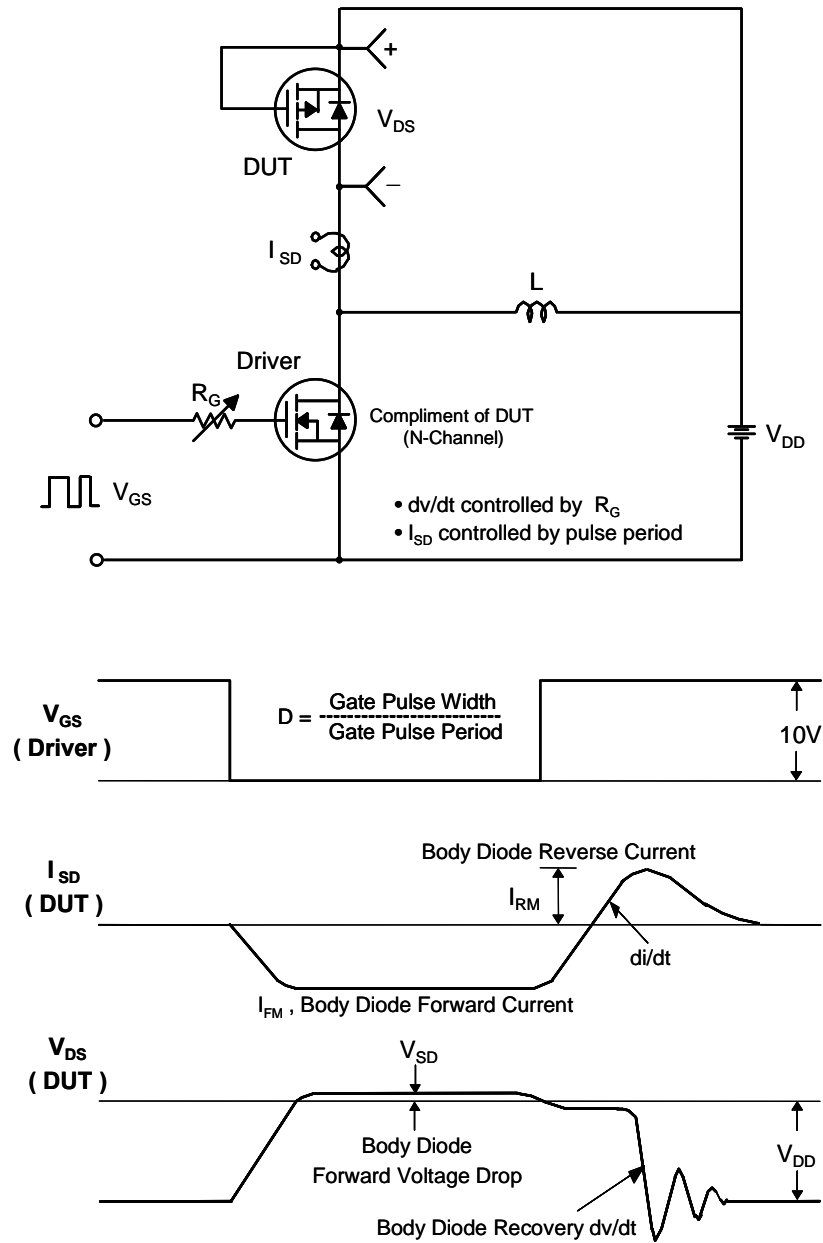
### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms

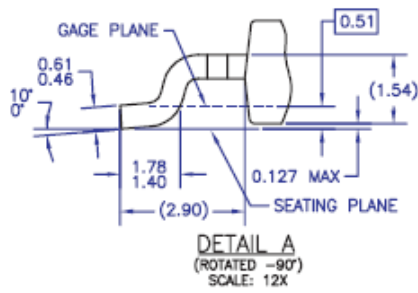
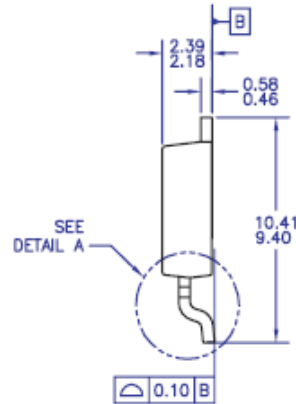
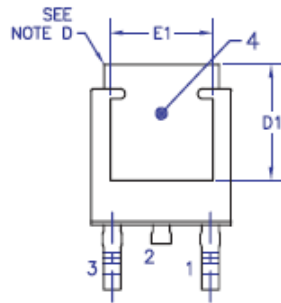
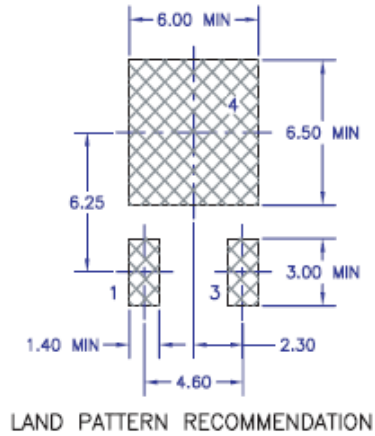
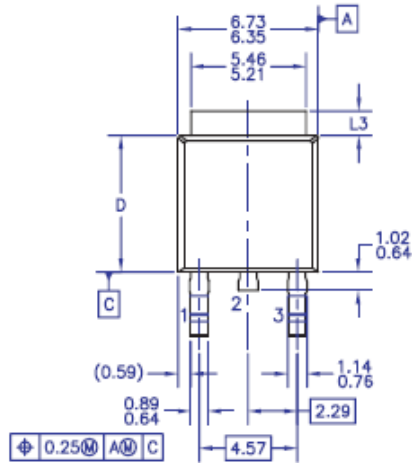


# Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Mechanical Dimensions

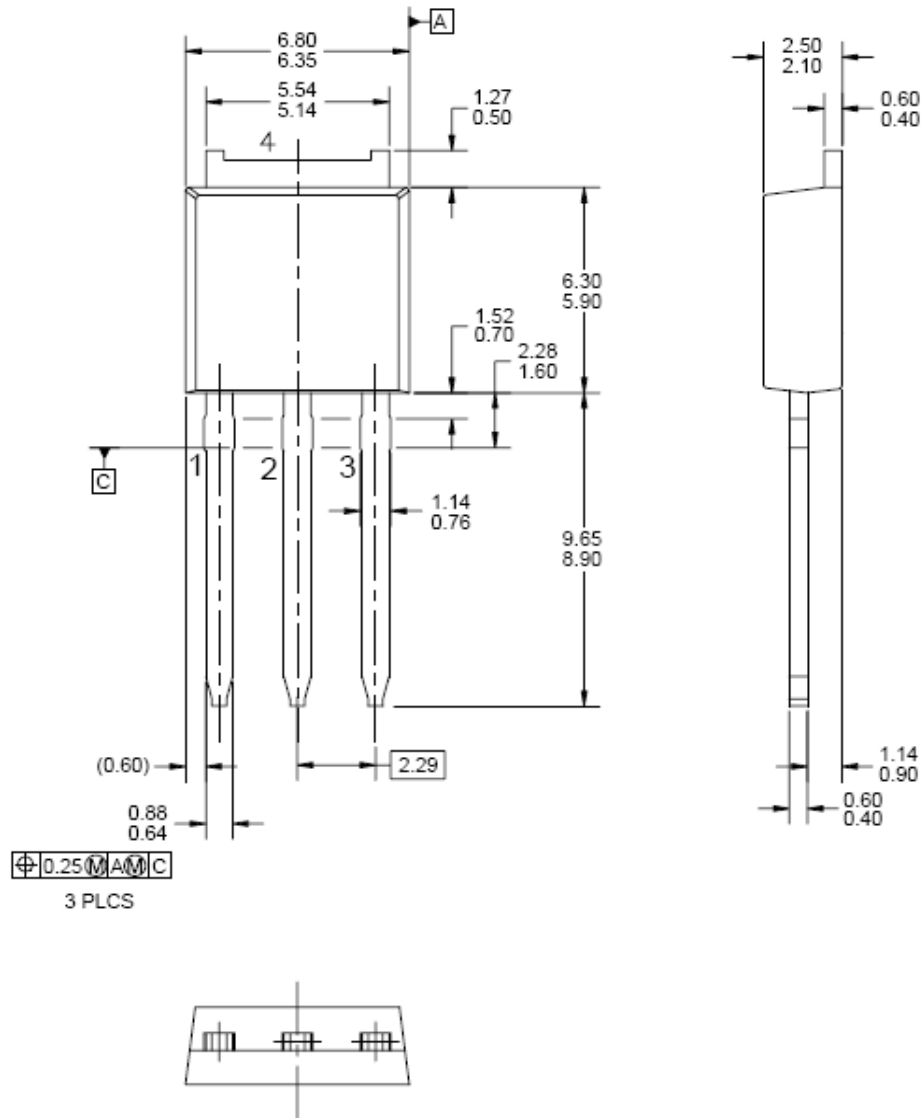
## D - PAK



Dimensions in Millimeters

# Mechanical Dimensions

## I - PAK



Dimensions in Millimeters

## TRADEMARKS


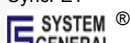
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